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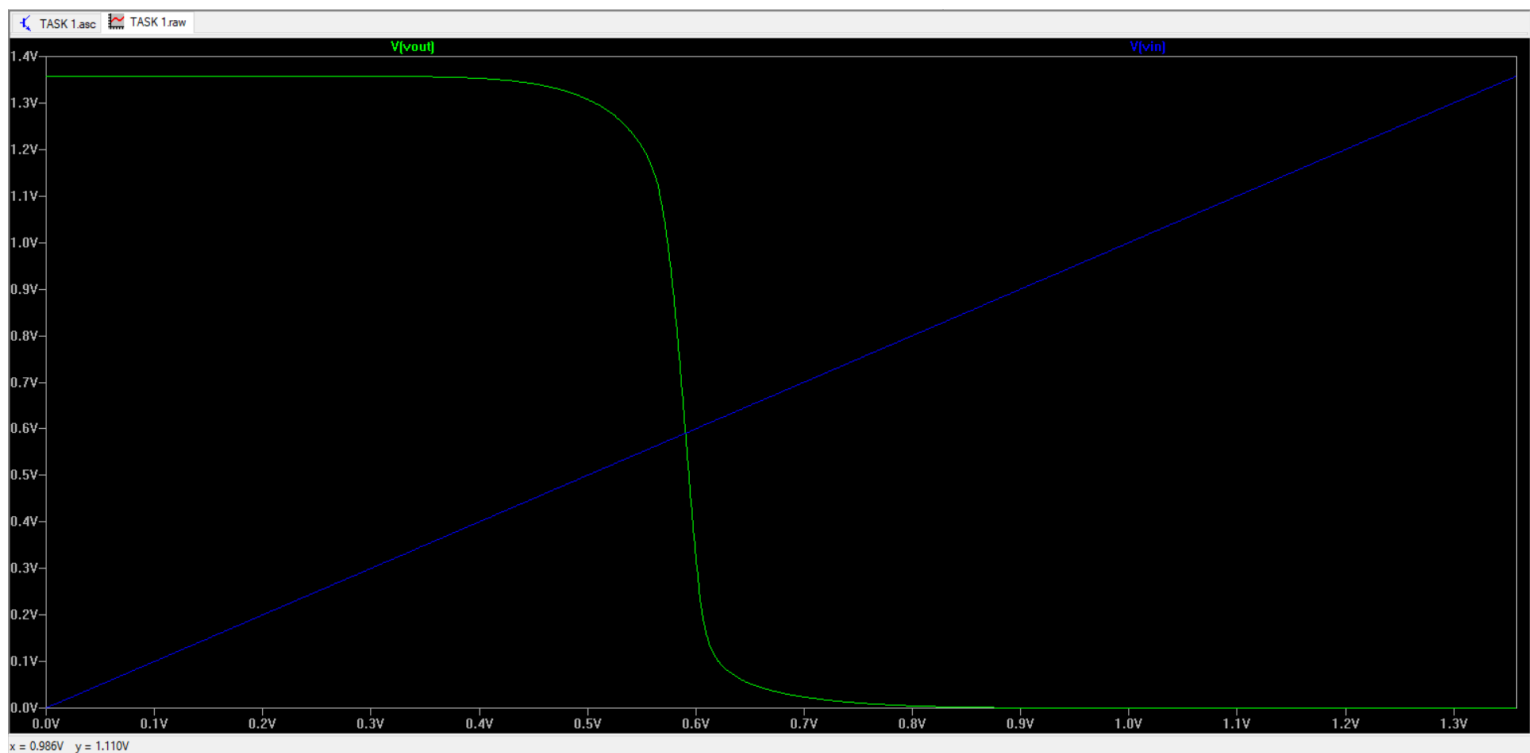
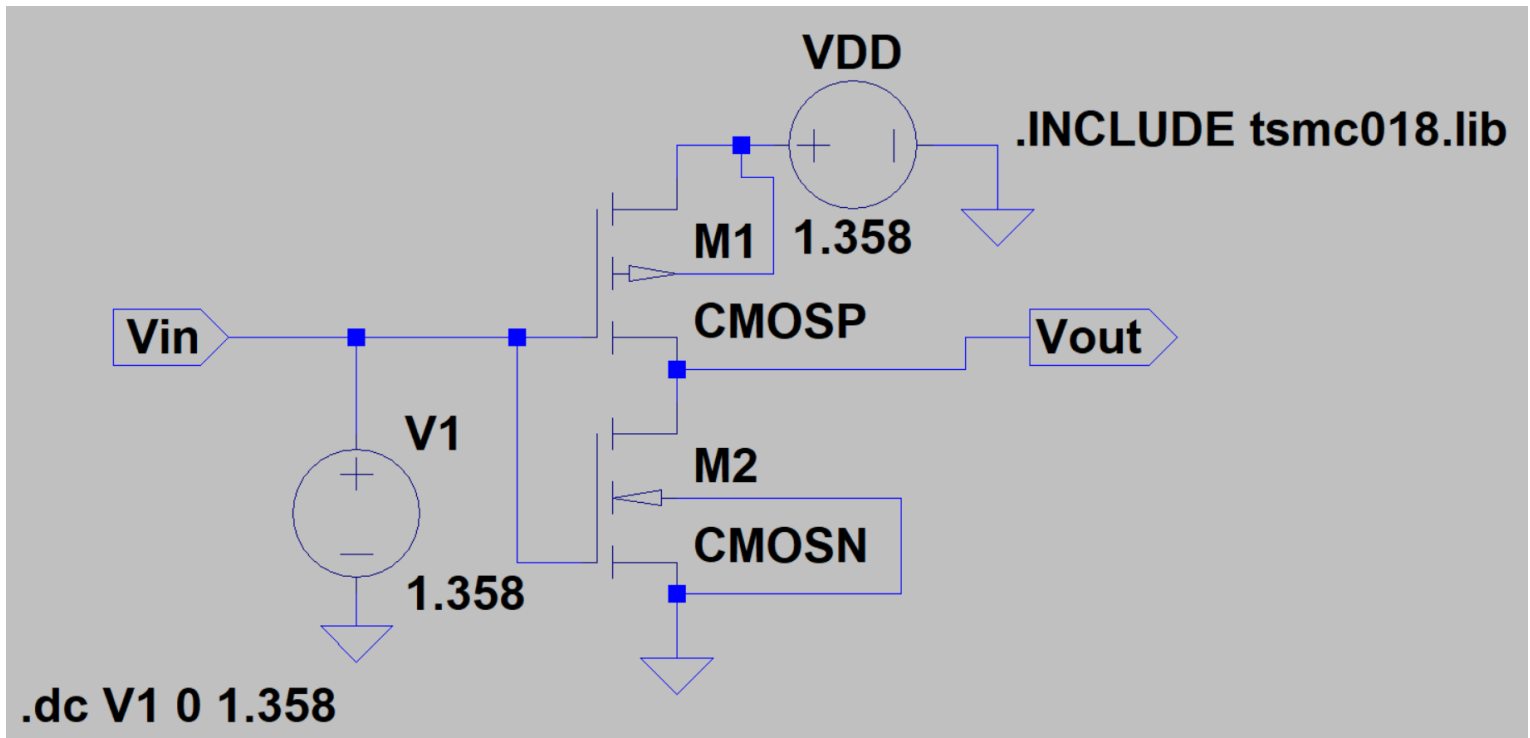
Reg.No	19BEC0358		
Student Name	ARPIT PATAWAT		
Course Code	ECE3002	Slot & Semester	L43+L44 WINTER -- 2021-22
Course Name	VLSI system design		
Program Title	Lab Assignment 3		
Faculty	Dr. Ragunath G		

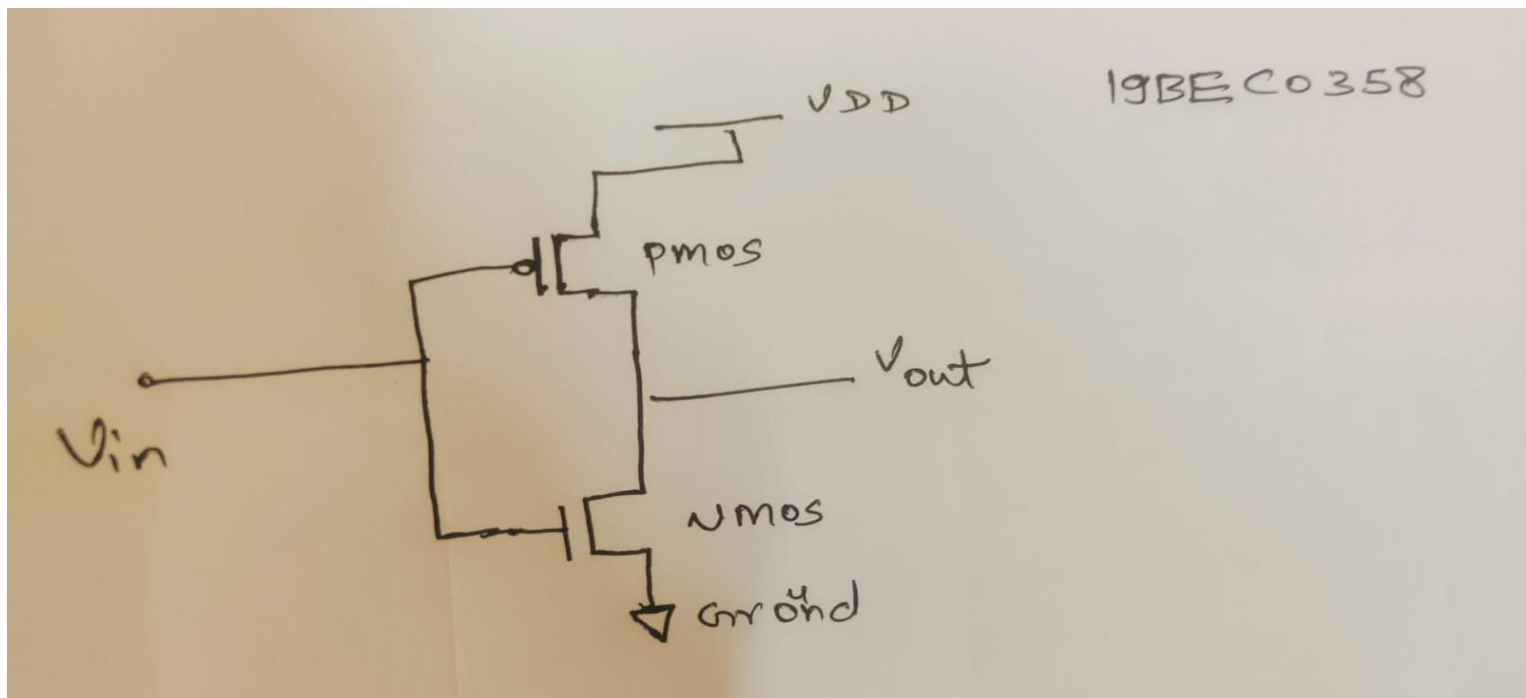
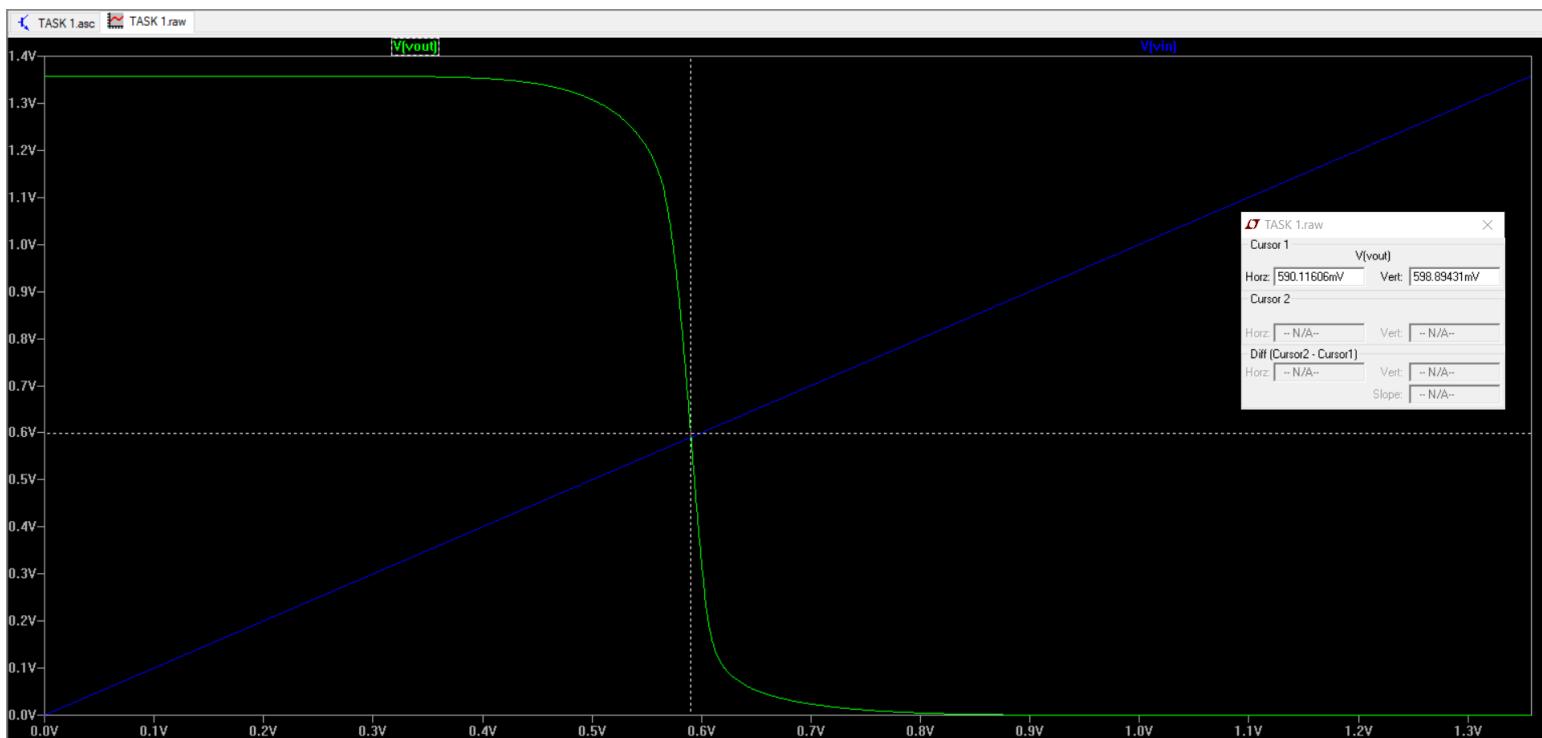
School of Electronics Engineering ,VIT, Vellore

1).

Aim → to plot the voltage transfer characteristics of CMOS inverter

Circuit Diagram → length = 180 nm, Width = 400nm(PMOS and NMOs)





Threshold voltage = 598.89mV (at PMOS width of 400nm)

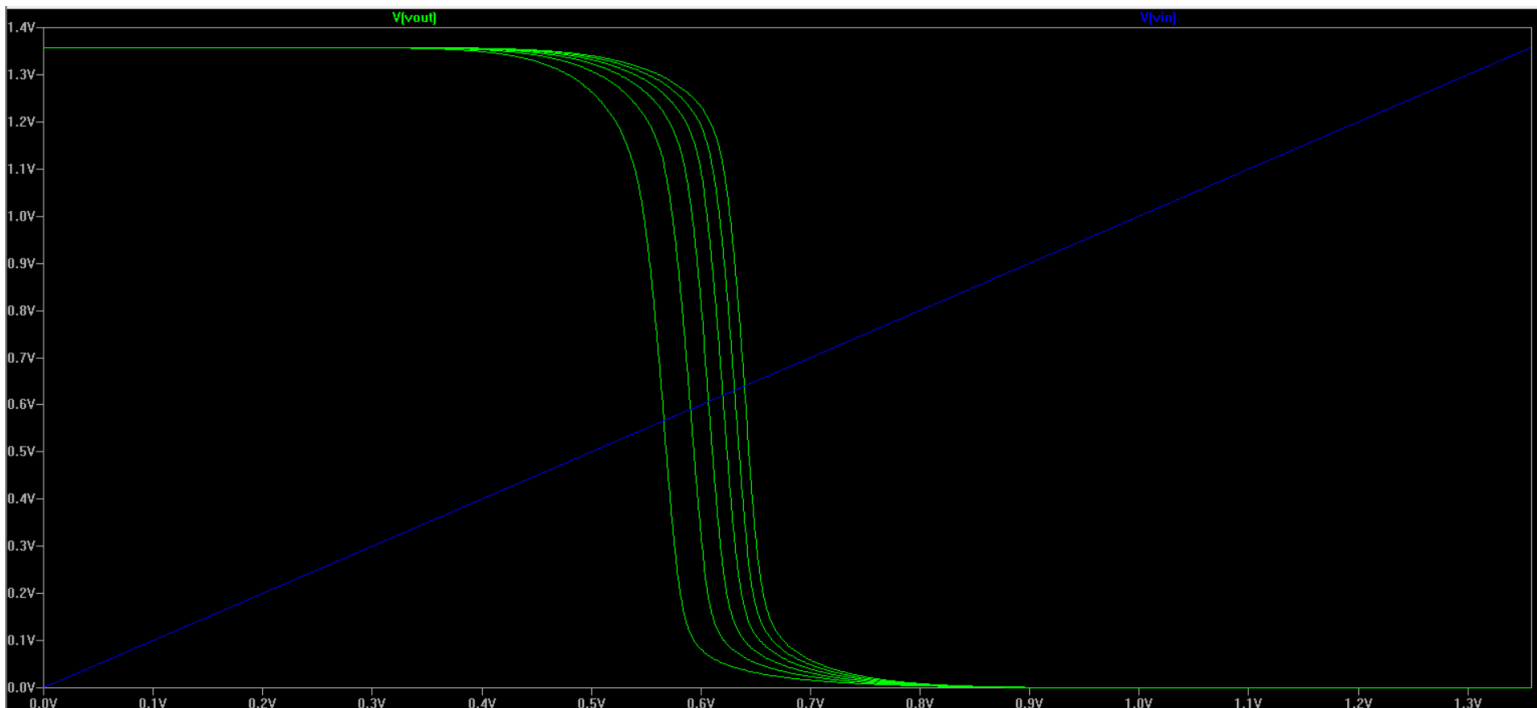
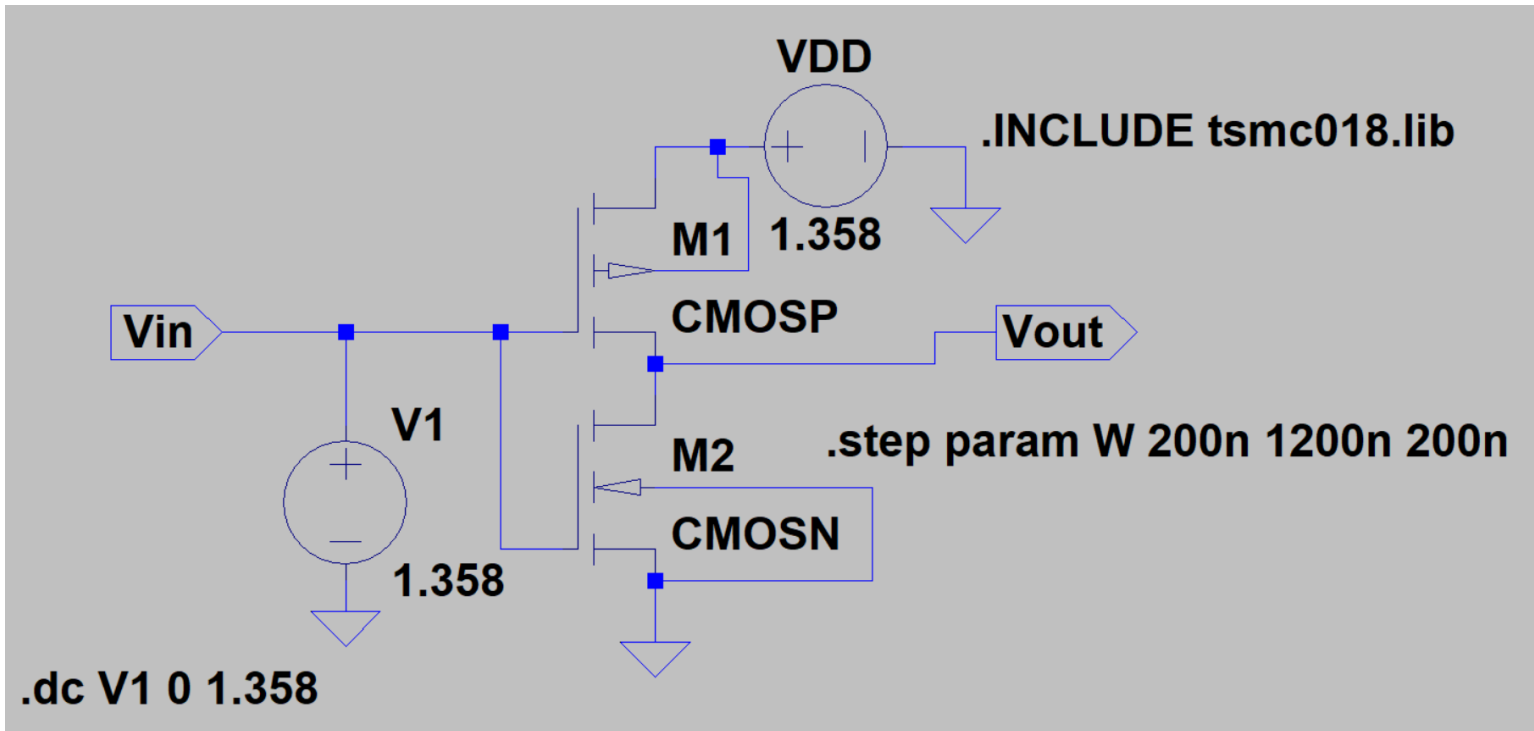
Result →

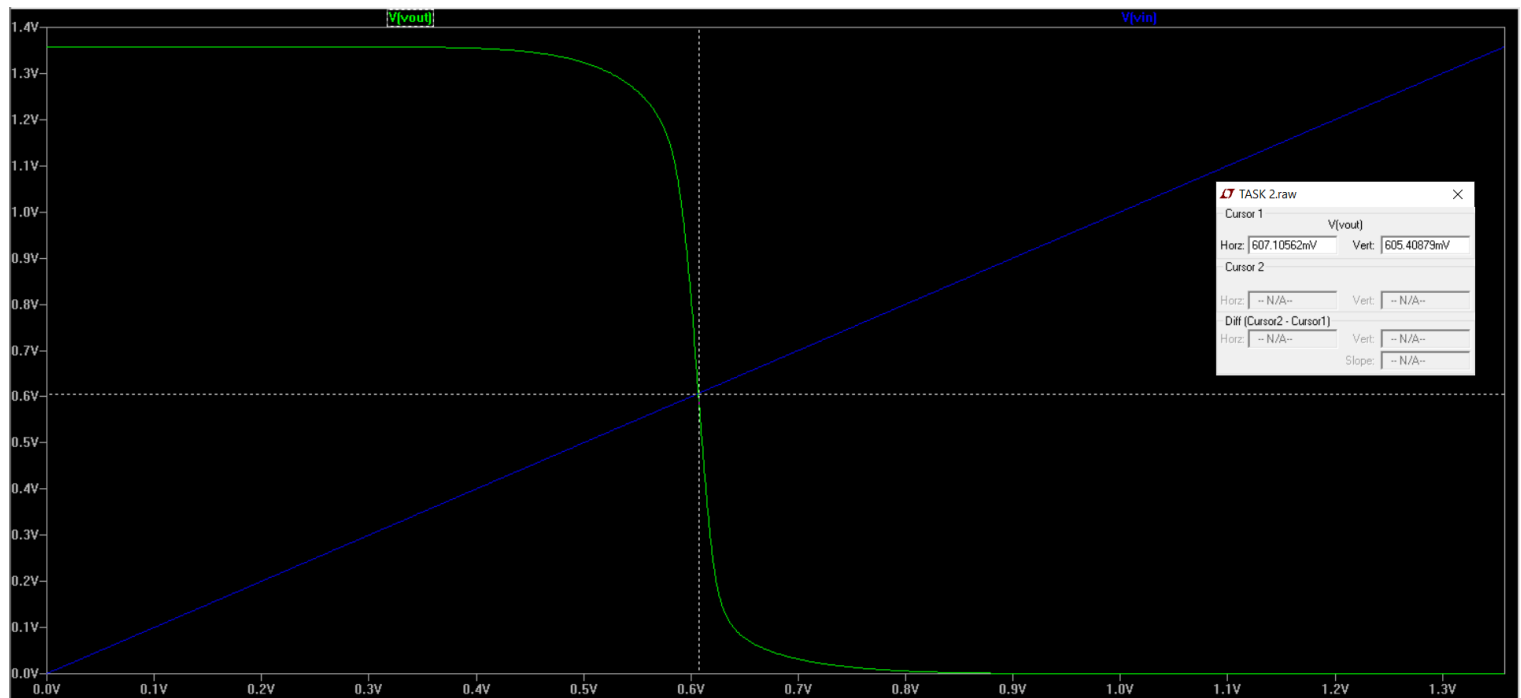
Threshold voltage is expected to be half of VDD. Here I took VDD = 1.358 so expected threshold voltage is 0.679mV but due to value of width of PMOS it is less than expected (598mV approx.). Hence, I was able to visualize the DC characteristics of CMOS inverter.

2).

Aim → to plot the voltage transfer characteristics of CMOS inverter for different width of PMOS

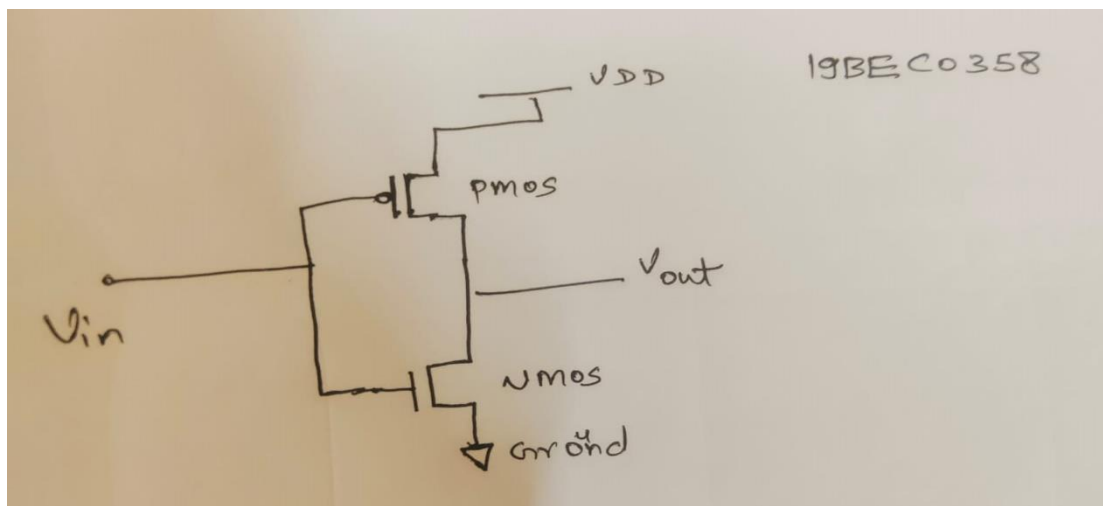
Circuit Diagram → length = 180 nm, Width (NMOS) = 400nm





At 600nm width of PMOS ↑

S. No.	PMOS Width	Threshold Voltage of the CMOS inverter
1	400n	598.89mV
2	600n	605.40mV
3	800n	620.23mV
4	1000n	634.61mV
5	1200n	639.73mV



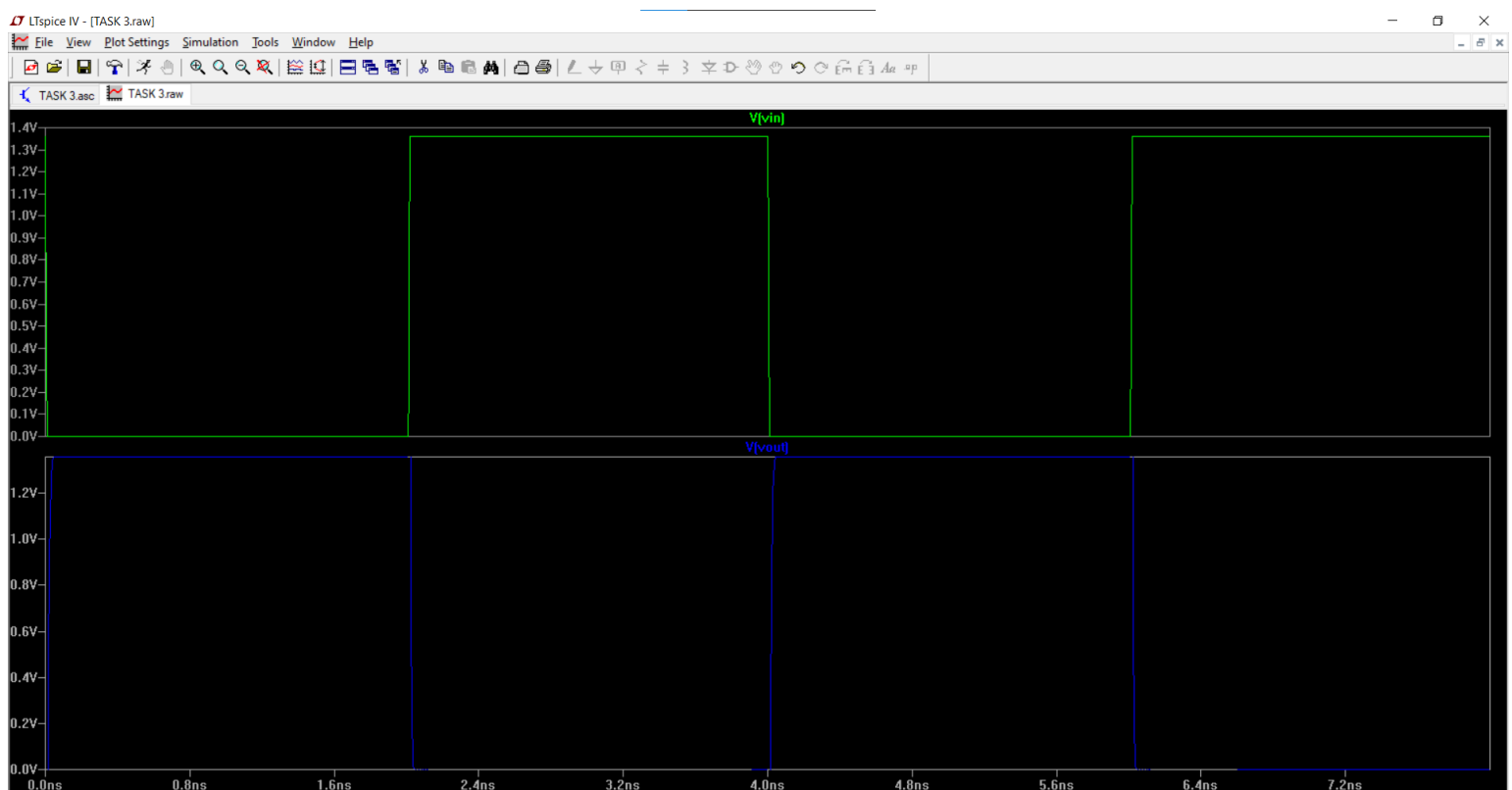
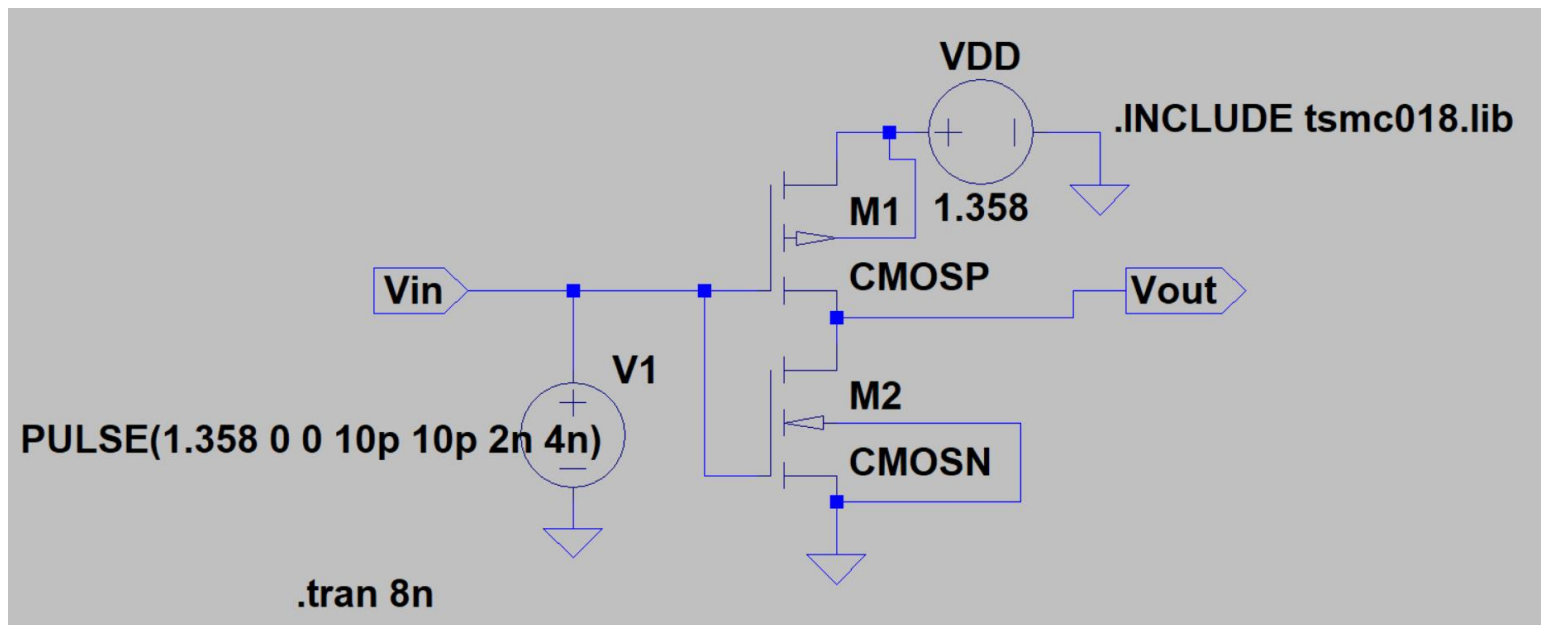
Result →

As the width of PMOS starts increasing, the threshold voltage of inverter also increases.

3).

Aim → to plot the Pulse input inverter characteristics

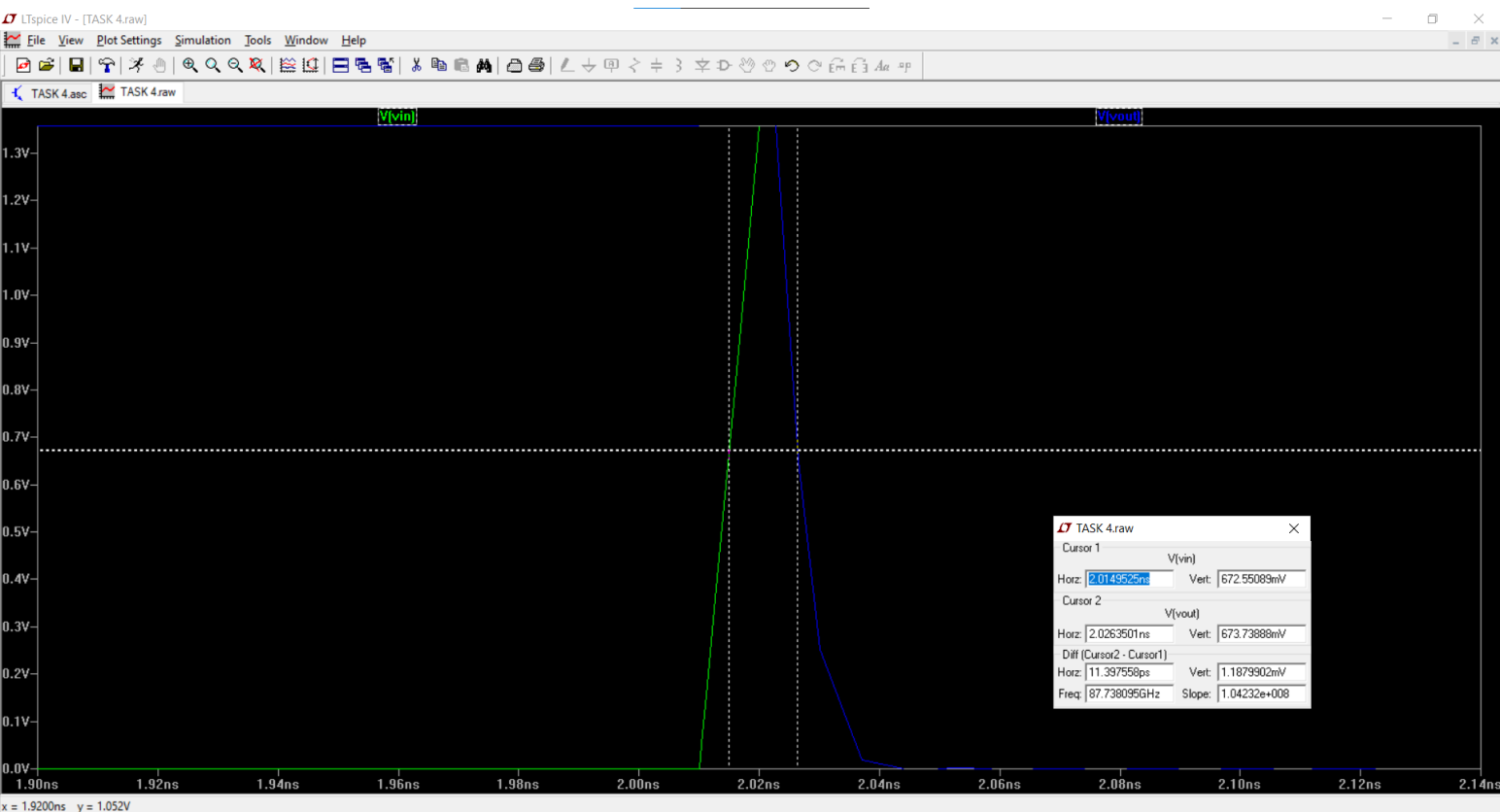
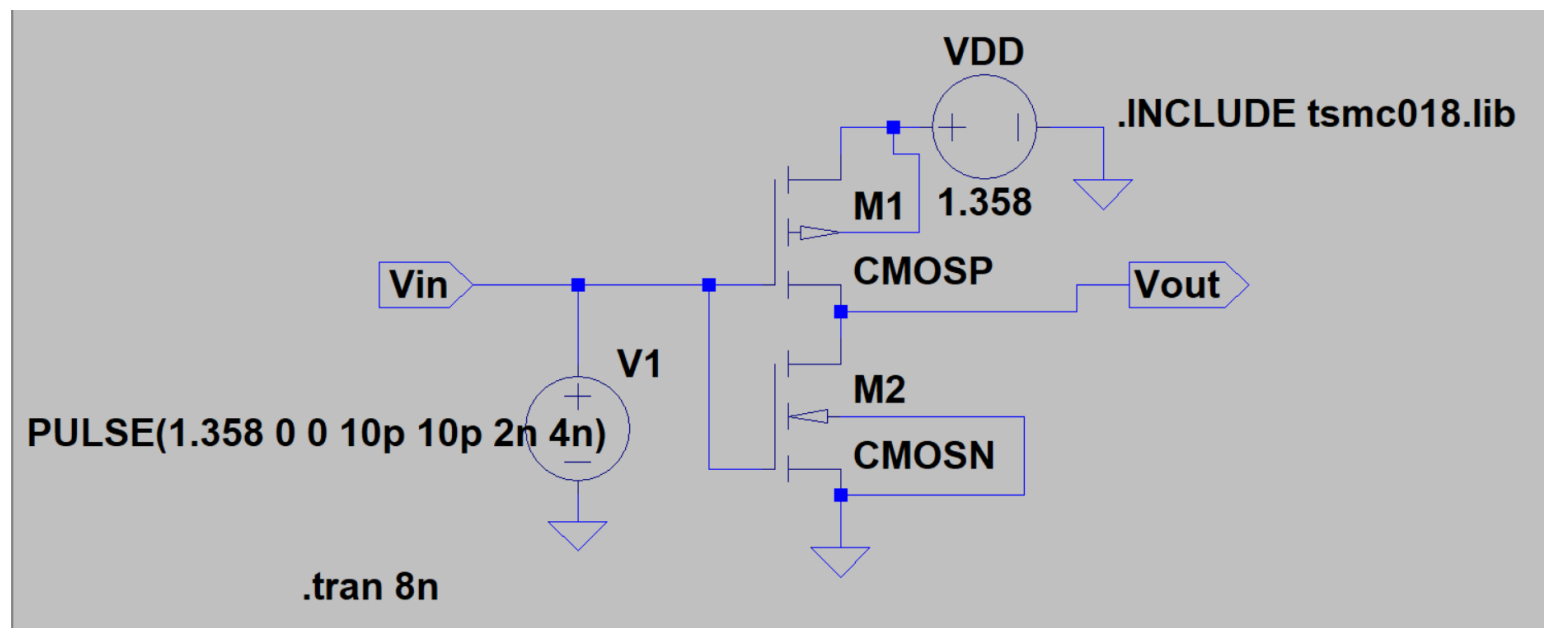
Circuit Diagram → length = 180 nm, Width (NMOS) = 400nm, Width (PMOS) = 400nm



Result → CMOS inverter output waveform is as expected (compliment of input)

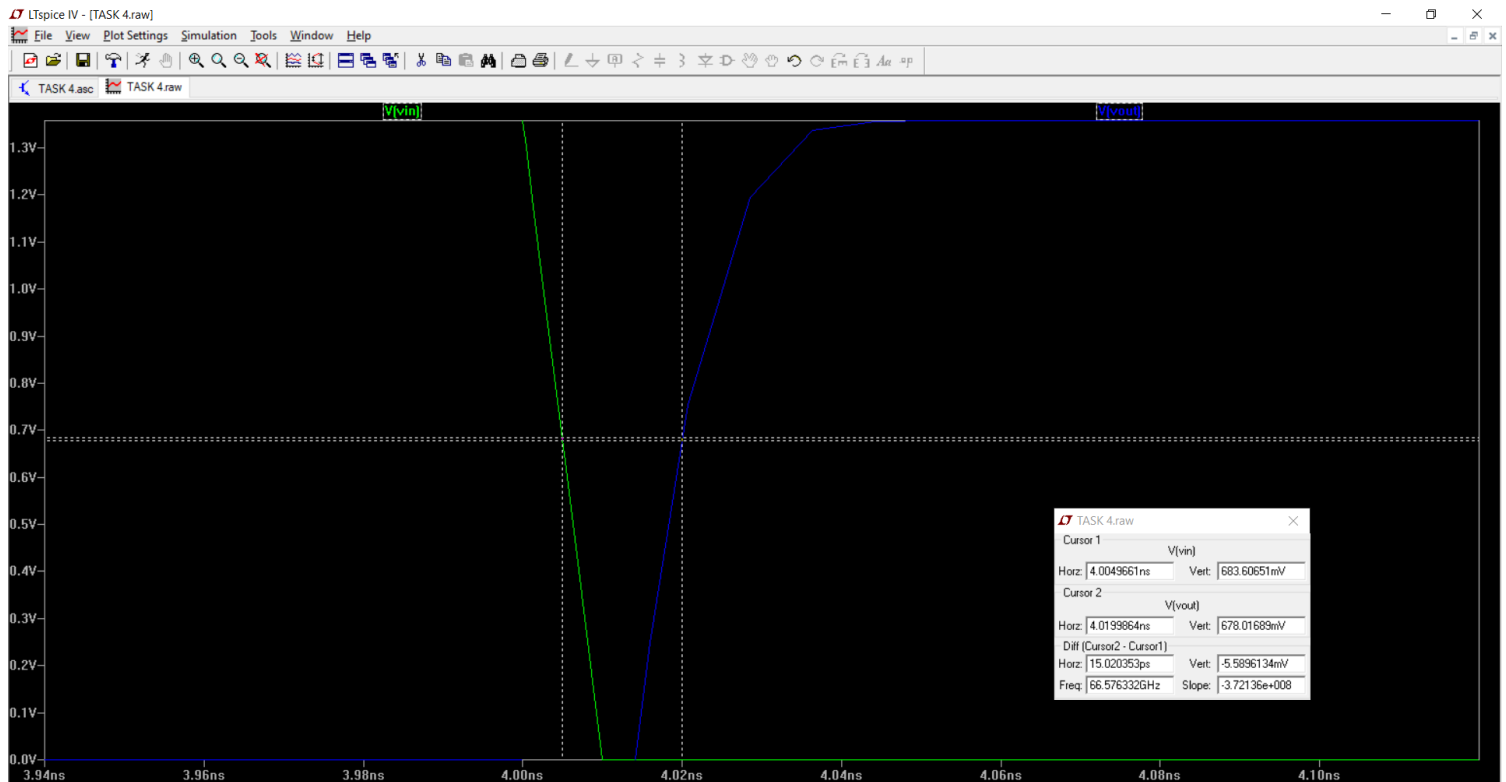
4).

Aim → to find rise time, fall time and propagation delay



Green – input wave, blue – output wave

TPDF = 11.397ps



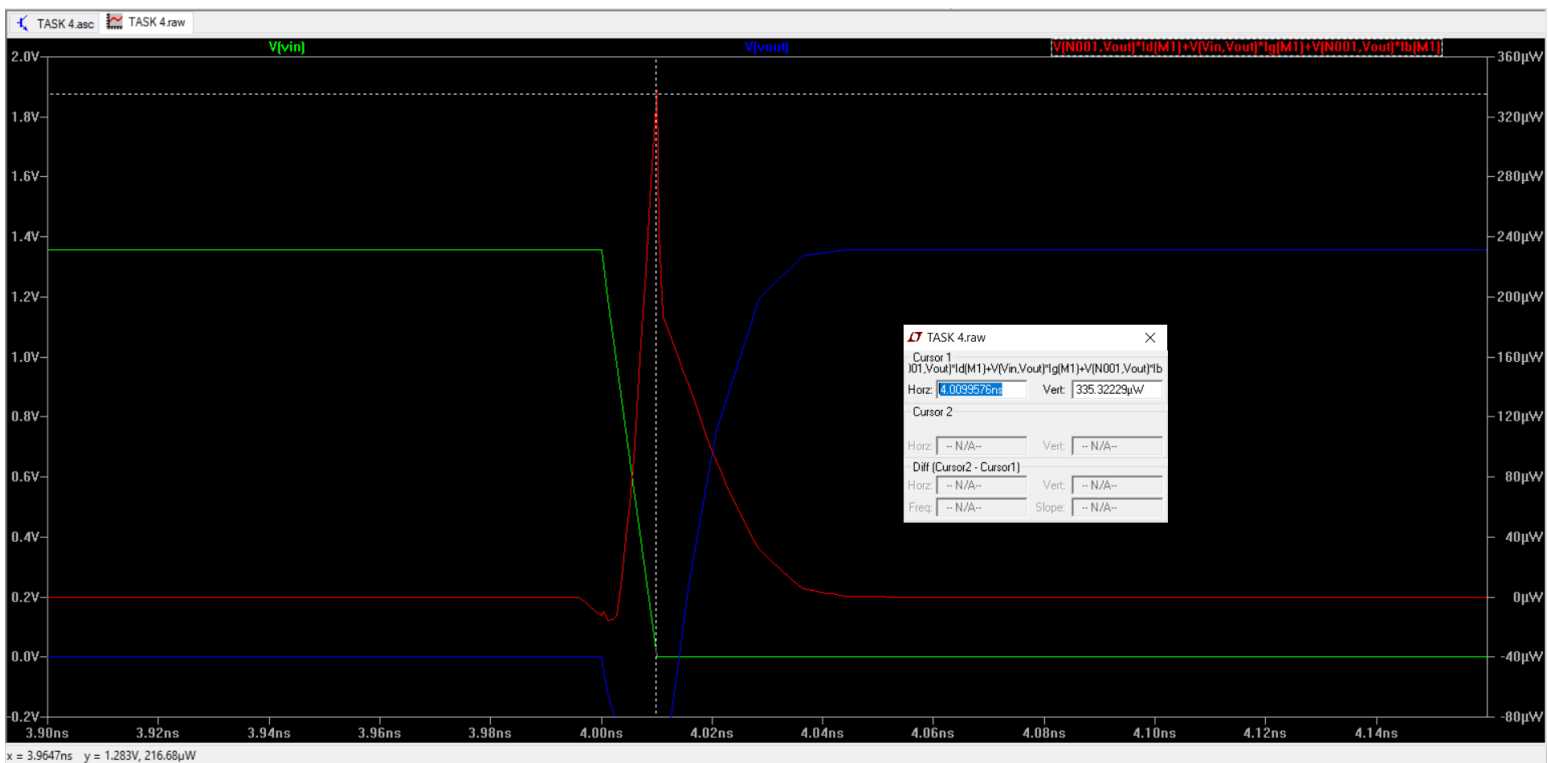
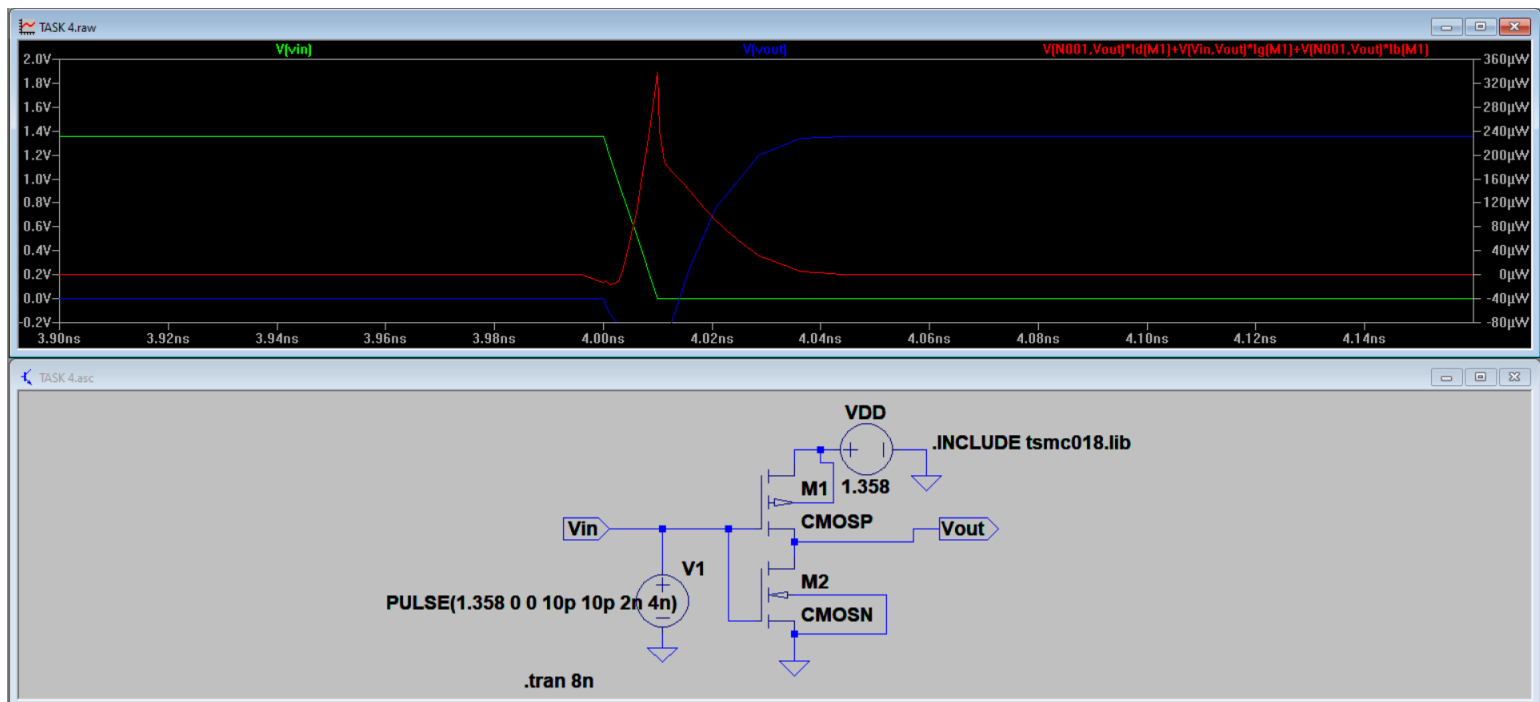
TPDR = 15.020ps

TPDF	11.397ps
TPDR	15.020ps
Propagation delay TPD	13.2085ps

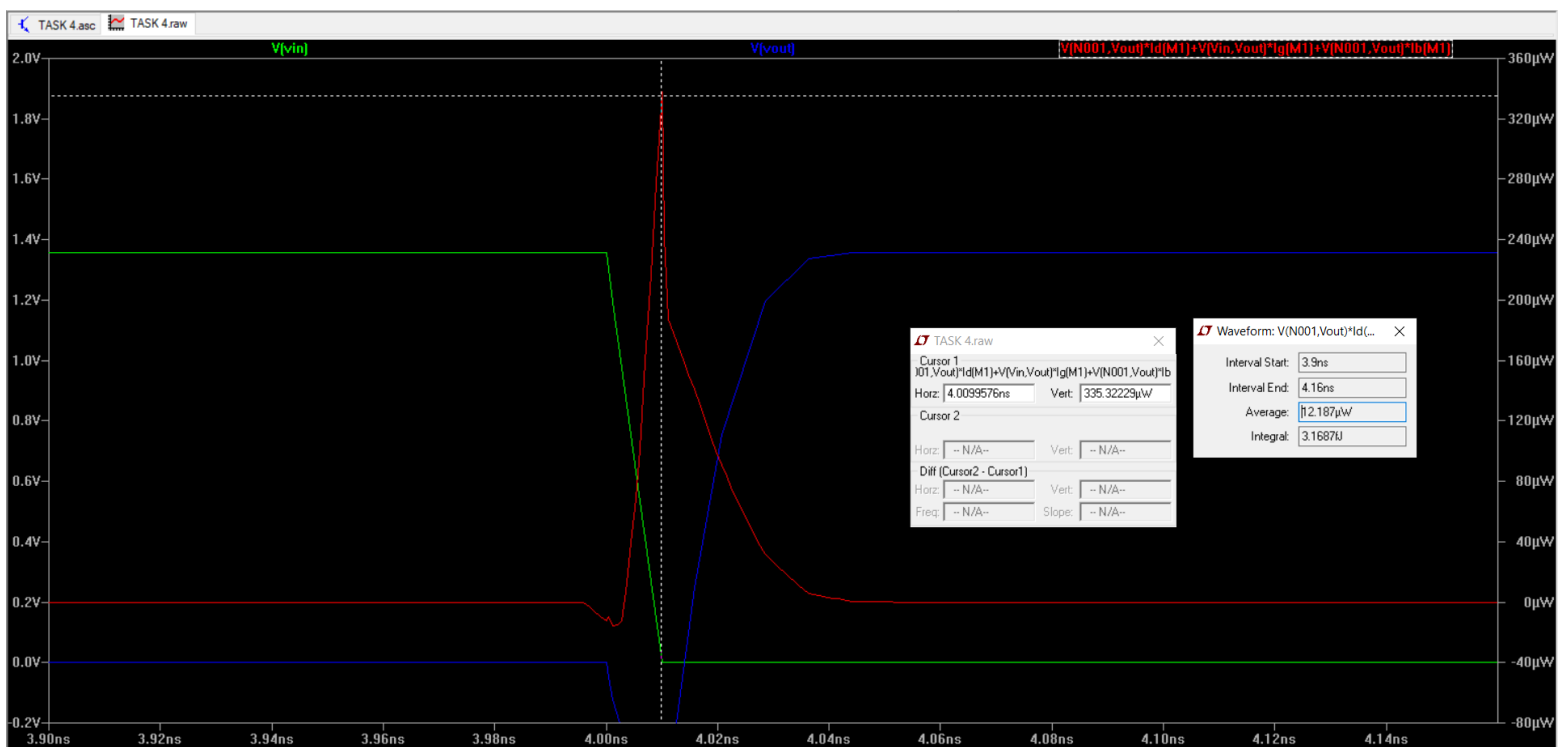
Result → TPD is average of TPDF and TPDR

3).

Aim → to plot output power signal and observe peak and average power



Peak power = 335.32micro watt



Average power = 12.187micro watt

5)

Aim → to design a 5-variable function

Circuit Diagram → length = 180 nm,

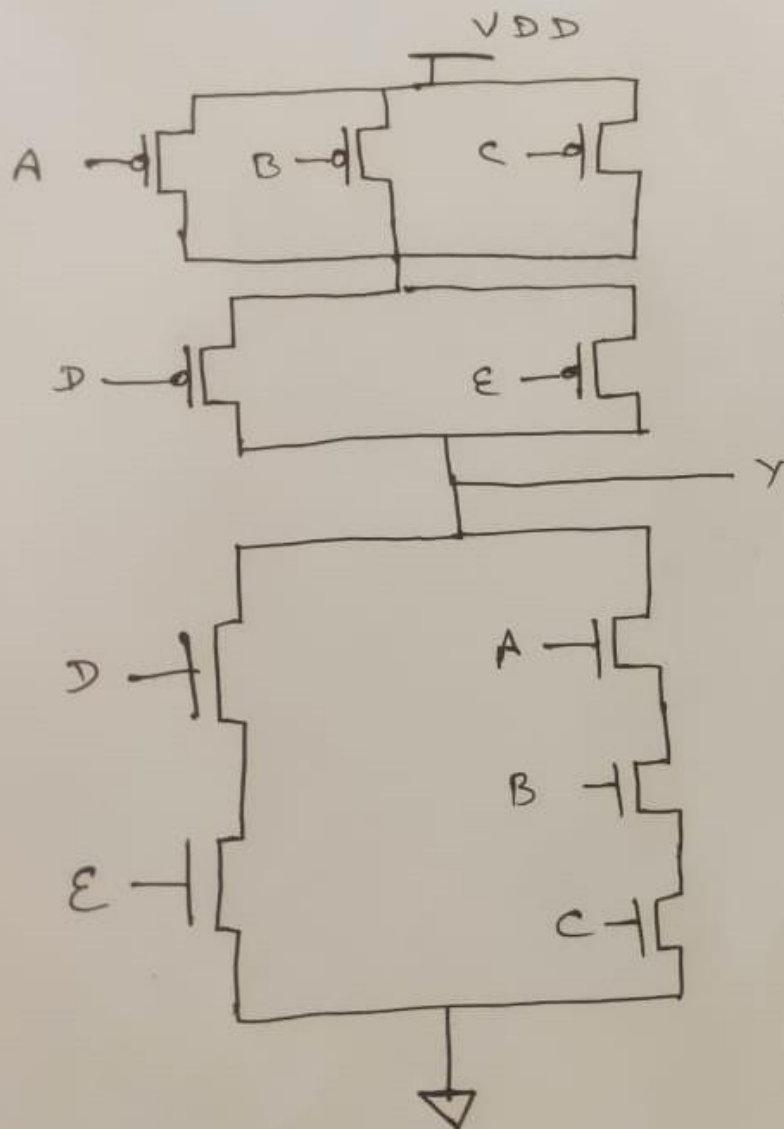
Here I took $Y = ((A.B.C) + (D.E))'$ function

$$Y = \overline{(A.B.C) + (D.E)}$$

19BEC0358

Arpit Patawat

width of NMOS = 400n, Resistance = R
width of PMOS = 1200n, Resistance = 3R



for Pull up circuit

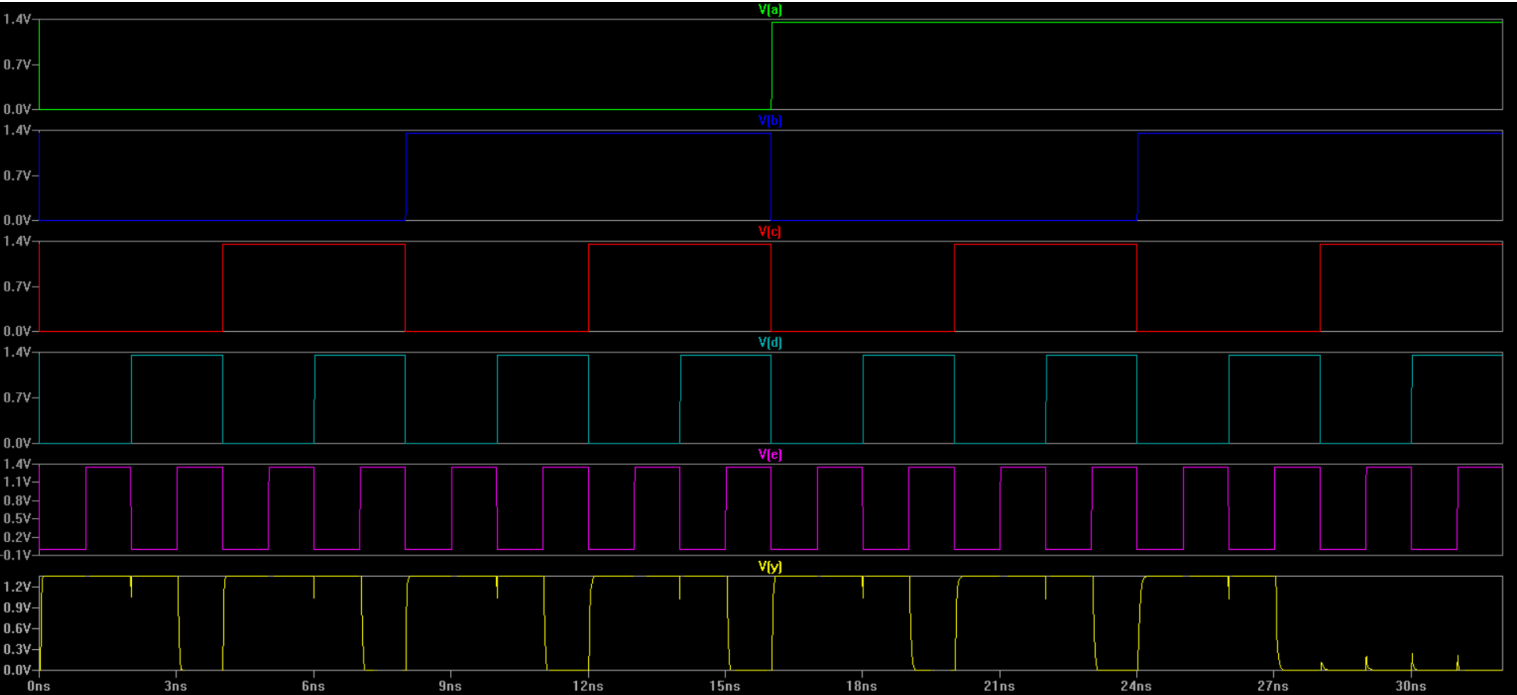
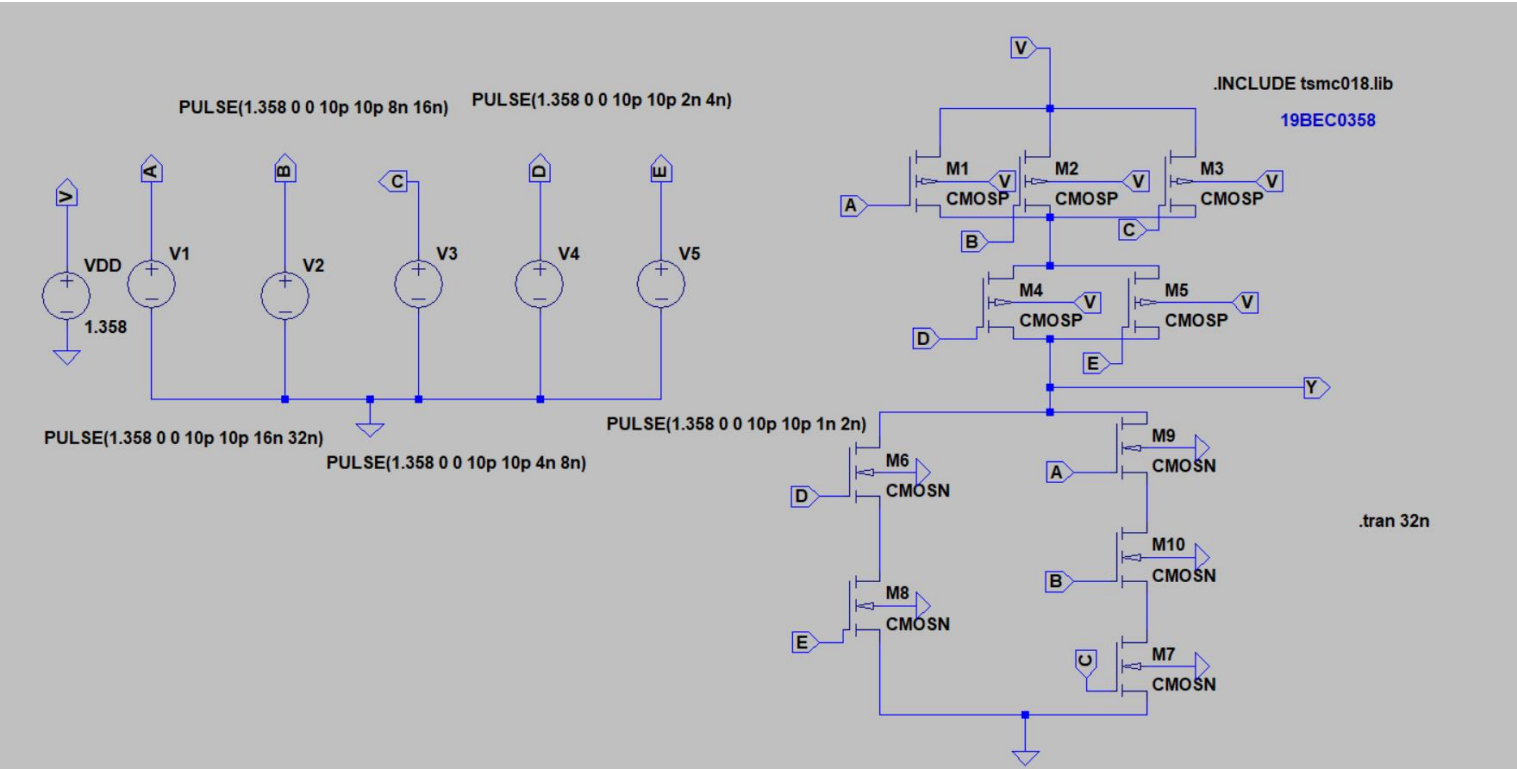
$$w_A = w_B = w_C = 2 \times 1200n, \frac{R}{2} \\ \Rightarrow (2400n, \frac{R}{2})$$

$$w_D = w_E = 2 \times 1200n, \frac{R}{2} \\ \Rightarrow (2400n, \frac{R}{2})$$

for Pull down ckt

$$w_A = w_B = w_C = 3 \times 400, \frac{R}{3} \\ \Rightarrow (1200n, \frac{R}{3})$$

$$w_D = w_E = 2 \times 400, \frac{R}{2} \\ \Rightarrow (800, \frac{R}{2})$$



Truth Table →

A	B	C	D	E	Y
0	0	0	0	0	1
0	0	0	0	1	1
0	0	0	1	0	1
0	0	0	1	1	0
0	0	1	0	0	1
0	0	1	0	1	1
0	0	1	1	0	1
0	0	1	1	1	0
0	1	0	0	0	1
0	1	0	0	1	1
0	1	0	1	0	1
0	1	0	1	1	0
0	1	1	0	0	1
0	1	1	0	1	1
0	1	1	1	0	1
0	1	1	1	1	0
1	0	0	0	0	1
1	0	0	0	1	1
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1	1	1	0	0	0
1	1	1	0	1	0
1	1	1	1	0	0
1	1	1	1	1	0

Result → our final output waveform matches with truth table. Hence, we were successfully able to build circuit using CMOS design.

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